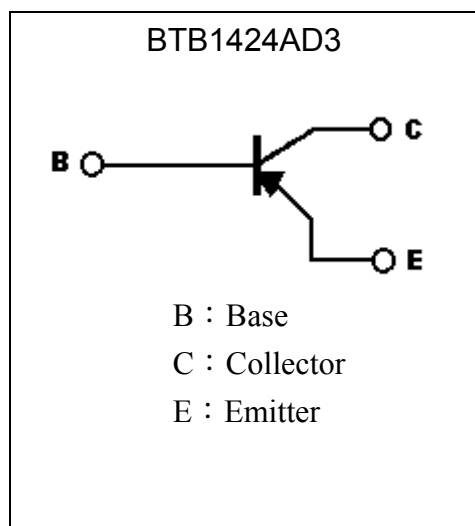
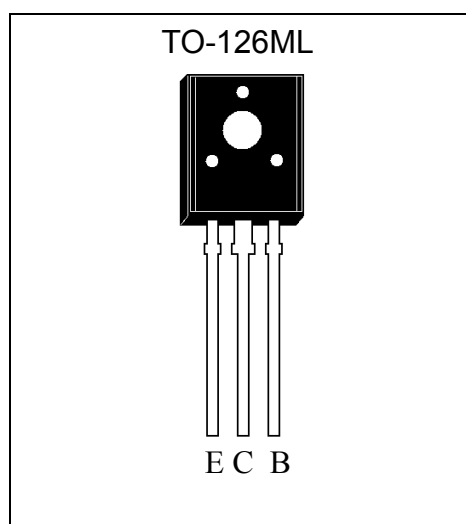


Low $V_{CE(sat)}$ PNP Epitaxial Planar Transistor

BTB1424AD3

Features

- Excellent DC current gain characteristics
- Low Saturation Voltage, $V_{CE(sat)} = -0.3V(\text{typ})$ @ $I_C = -2A$, $I_B = -100mA$.
- Complementary to BTB2150AD3
- Pb-free package

Symbol

Outline

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current(DC)	I_C	-3	A
Collector Current(Pulsed) (Note 1)	I_{CP}	-5	
Power Dissipation($T_A = 25^\circ\text{C}$)	P_d	1	W
Power Dissipation($T_C = 25^\circ\text{C}$)		10	
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$

Note 1: Single pulse, $P_w \leq 10\text{ms}$, Duty Cycle $\leq 30\%$.

**Characteristics** (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	-50	-	-	V	I _C =-50μA
BV _{CEO}	-50	-	-	V	I _C =-1mA
BV _{EBO}	-6	-	-	V	I _E =-50μA
I _{CBO}	-	-	-0.1	μA	V _{CB} =-20V
I _{EBO}	-	-	-0.1	μA	V _{EB} =-5V
*V _{CE(sat)}	-	-	-0.4	V	I _C =-1A, I _B =-50mA
*V _{CE(sat)}	-	-	-0.5	V	I _C =-2A, I _B =-100mA
*h _{FE}	82	-	560	-	V _{CE} =-2V, I _C =-500mA
f _T	-	240	-	MHz	V _{CE} =-2V, I _C =-500mA, f=100MHz
Cob	-	35	-	pF	V _{CB} =-10V, f=1MHz

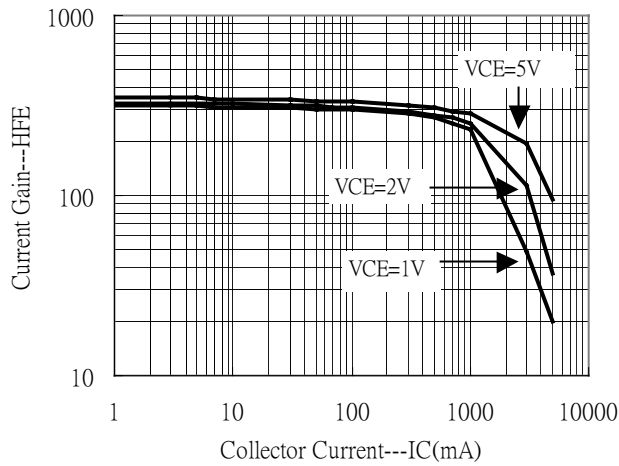
*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

Classification Of h_{FE}

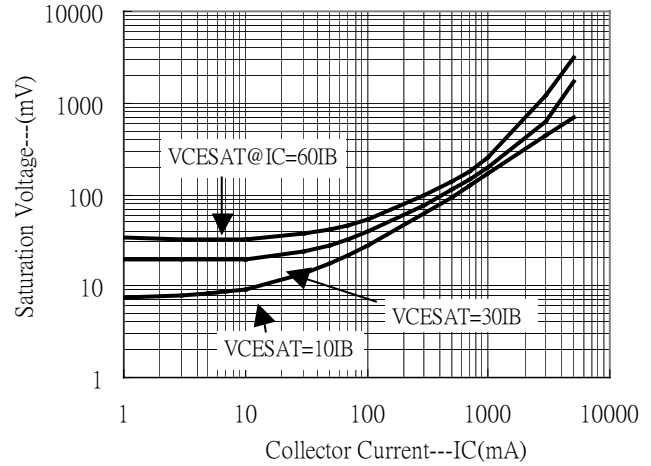
Rank	P	Q	R	S
h _{FE} range	82~180	120~270	180~390	270~560

Characteristic Curves

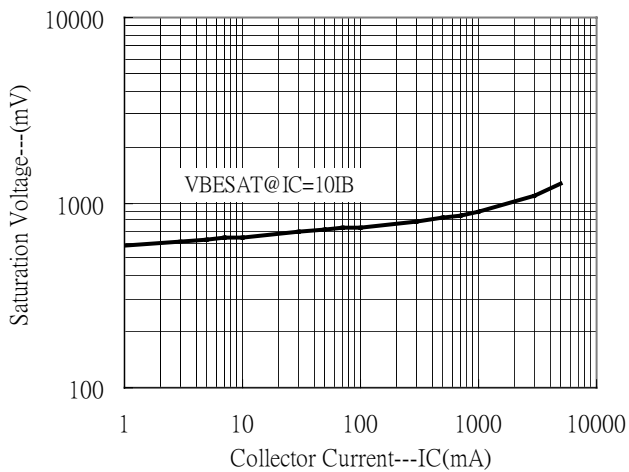
Current Gain vs Collector Current



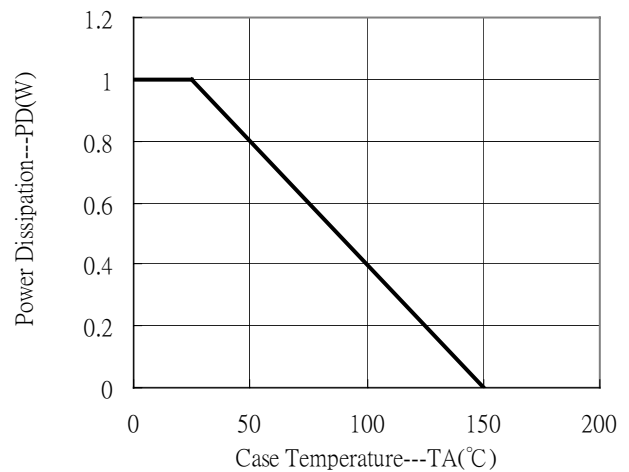
Saturation Voltage vs Collector Current



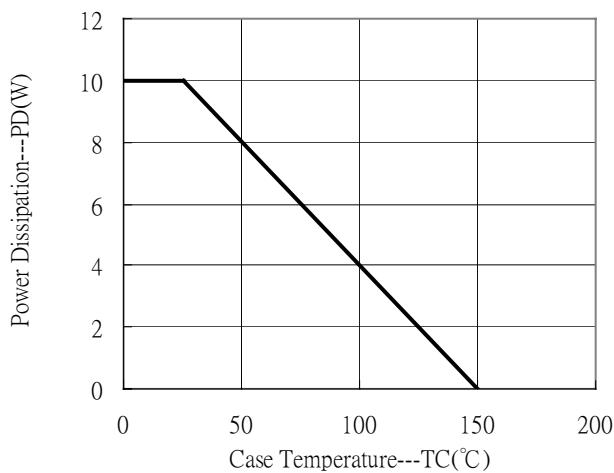
Saturation Voltage vs Collector Current



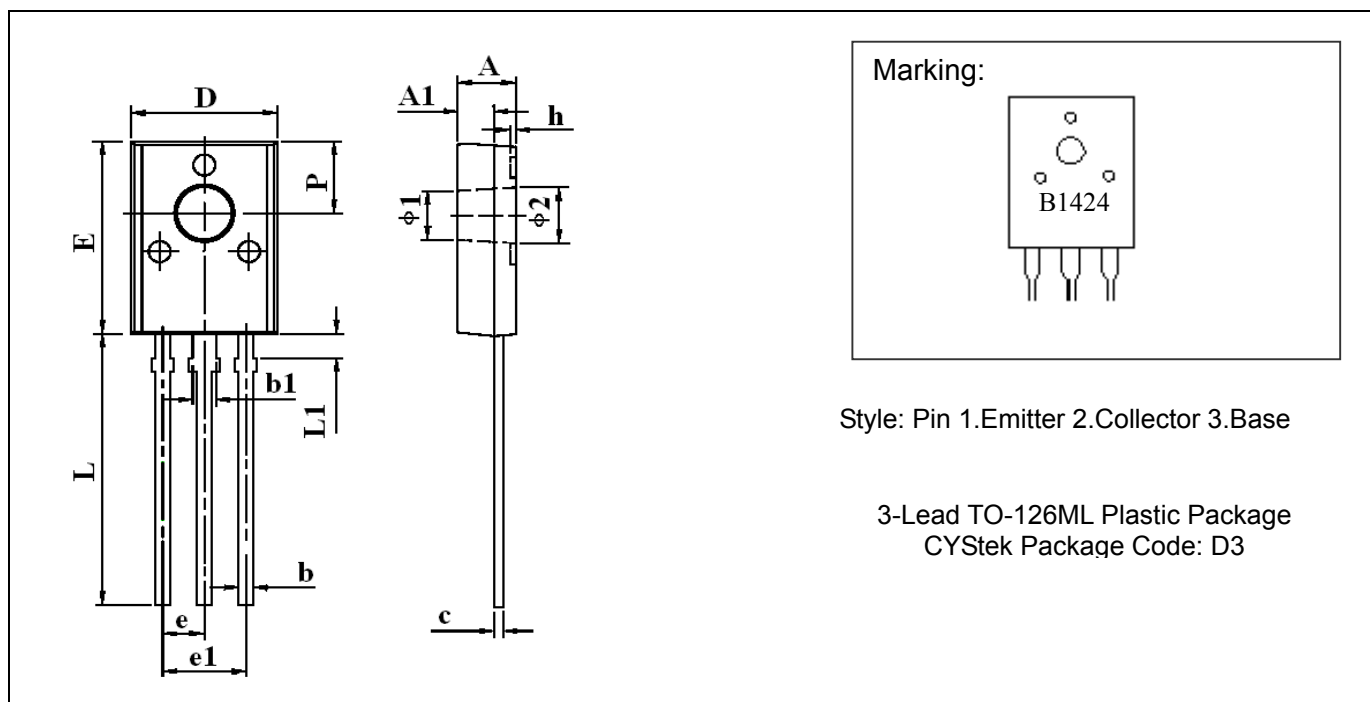
Power Derating Curve



Power Derating Curve



TO-126ML Dimension



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.118	0.134	3.000	3.400	e	*0.090		*2.28	
A1	0.071	0.087	1.800	2.200	e1	0.176	0.183	4.460	4.660
b	0.026	0.034	0.660	0.860	L	0.594	0.610	15.100	15.500
b1	0.046	0.054	1.170	1.370	L1	0.051	0.059	1.300	1.500
c	0.018	0.024	0.450	0.600	P	0.159	0.167	4.040	4.240
D	0.307	0.323	7.800	8.200	Φ ₁	0.118	0.126	3.000	3.200
E	0.425	0.441	10.800	11.200	Φ ₂	0.122	0.130	3.100	3.300

Notes: 1. Controlling dimension: millimeters.

2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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